

NLAS4685

Ultra-Low Resistance Dual SPDT Analog Switch

The NLAS4685 is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low R_{ON} of 0.8 Ω , for the Normally Closed (NC) switch and for the Normally Opened switch (NO) at 2.7 V.

The part also features guaranteed Break Before Make switching, assuring the switches never short the driver.

The NLAS4685 is available in a 2.0 x 1.5 mm bumped die array, with a 3 x 4 arrangement of solder bumps. The pitch of the solder bumps is 0.5 mm for easy handling.

Features

- Ultra-Low R_{ON} , < 0.8 Ω at 2.7 V
- Threshold Adjusted to Function with 1.8 V Control at $V_{CC} = 2.7\text{--}3.3$ V
- Single Supply Operation from 1.8–5.5 V
- Tiny 2 x 1.5 mm Bumped Die
- Low Crosstalk, < 81 dB at 100 kHz
- Full 0– V_{CC} Signal Handling Capability
- High Isolation, –65 dB at 100 kHz
- Low Standby Current, < 50 nA
- Low Distortion, < 0.14% THD
- R_{ON} Flatness of 0.15 Ω
- Pin for Pin Replacement for MAX4685
- Pb-Free Package is Available

Applications

- Cell Phone
- Speaker Switching
- Power Switching (Up to 100 mA)
- Modems
- Automotive



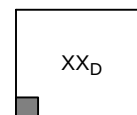
ON Semiconductor®

<http://onsemi.com>



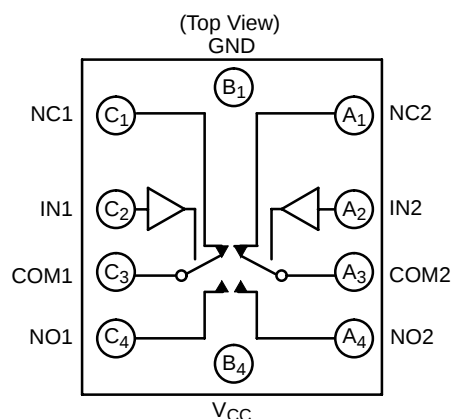
A1
Microbump-10
CASE 489AA

MARKING DIAGRAM



A1
XX = Device Code
D = Date Code

PIN CONNECTIONS AND LOGIC DIAGRAM



FUNCTION TABLE

IN 1, 2	NO 1, 2	NC 1, 2
0	OFF	ON
1	ON	OFF

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS4685FCT1	Microbump	3000 Tape/Reel
NLAS4685FCT1G	Microbump (Pb-Free)	3000 Tape/Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	− 0.5 to +7.0	V
V _{IS}	Analog Input Voltage (V _{NO} , V _{NC} , or V _{COM}) (Note 1)	−0.5 ≤ V _{IS} ≤ V _{CC} + 0.5	V
V _{IN}	Digital Select Input Voltage	− 0.5 ≤ V _I ≤ +7.0	V
I _{IK}	DC Current, Into or Out of Any Pin	± 50	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Signal voltage on NC, NO, and COM exceeding V_{CC} or GND are clamped by the internal diodes. Limit forward diode current to maximum current rating.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	1.8	5.5	V
V _{IN}	Digital Select Input Voltage	GND	5.5	V
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V _{CC}	V
T _A	Operating Temperature Range	−55	+125	°C
t _r , t _f	Input Rise or Fall Time, SELECT	V _{CC} = 3.3 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V		ns/V
		0	100	
		0	20	

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V _{CC} ± 10%	Guaranteed Limit			Unit
				−55°C to 25°C	< 85°C	< 125°C	
V _{IH}	Minimum High-Level Input Voltage, Select Inputs		2.0	1.4	1.4	1.4	V
			2.5	1.4	1.4	1.4	
			3.0	1.4	1.4	1.4	
			5.0	2.0	2.0	2.0	
V _{IL}	Maximum Low-Level Input Voltage, Select Inputs		2.0	0.5	0.5	0.5	V
			2.5	0.5	0.5	0.5	
			3.0	0.5	0.5	0.5	
			5.0	0.8	0.8	0.8	
I _{IN}	Maximum Input Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	5.5	± 1.0	± 1.0	± 1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or GND	0	± 10	± 10	± 10	μA
I _{CC}	Maximum Quiescent Supply Current	Select and V _{IS} = V _{CC} or GND	5.5	± 180	± 200	± 200	nA

DC ELECTRICAL CHARACTERISTICS – Analog Section

Symbol	Parameter	Condition	V _{CC} ± 10%	Guaranteed Maximum Limit						Unit
				−55°C to 25°C		< 85°C		< 125°C		
				Min	Max	Min	Max	Min	Max	
R _{ON} (NC, NO)	“ON” Resistance (Note 2)	V _{IN} ≥ V _{IH}	2.5		2.0		2.0		2.0	Ω
		V _{IS} = GND to V _{CC}	3.0		0.8		0.8		1.0	
		I _{IN} ≤ 100 mA	5.0		0.8		0.8		0.9	
R _{FLAT} (NC, NO)	On-Resistance Flatness (Notes 2, 4)	I _{COM} = 100 mA	2.5		0.35		0.35		0.35	Ω
		V _{IS} = 0 to V _{CC}	3.0		0.35		0.35		0.35	
			5.0		0.35		0.35		0.35	
ΔR _{ON}	On-Resistance Match Between Channels (Notes 2 and 3)	V _{IS} = 1.3 V; I _{COM} = 100 mA	2.5		0.18		0.18		0.18	Ω
		V _{IS} = 1.5 V; I _{COM} = 100 mA	3.0		0.06		0.06		0.06	
		V _{IS} = 2.8 V; I _{COM} = 100 mA	5.0		0.06		0.06		0.06	
I _{NC(OFF)} I _{NO(OFF)}	NC or NO Off Leakage Current (Figure 10)	V _{IN} = V _{IL} or V _{IH} V _{NO} or V _{NC} = 1.0 V _{COM} = 4.5 V	5.5	−1	1	−10	10	−150	150	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 10)	V _{IN} = V _{IL} or V _{IH} V _{NO} 1.0 V or 4.5 V with V _{NC} floating or V _{NC} 1.0 V or 4.5 V with V _{NO} floating V _{COM} = 1.0 V or 4.5 V	5.5	−1	1	−10	10	−150	150	nA

2. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
3. $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$ between all switches.
4. Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	V _{CC} (V)	V _{IS} (V)	Guaranteed Maximum Limit						Unit	
					– 55°C to 25°C			< 85°C		< 125°C		
					Min	Typ*	Max	Min	Max	Min		Max
t _{ON}	Turn-On Time	R _L = 50 Ω, C _L = 35 pF (Figures 2 and 3)	2.5 3.0 5.0	1.3 1.5 2.8			55 50 30		65 60 35		70 60 35	ns
t _{OFF}	Turn-Off Time	R _L = 50 Ω, C _L = 35 pF (Figures 2 and 3)	2.5 3.0 5.0	1.3 1.5 2.8			55 50 25		65 60 30		70 60 30	ns
t _{BBM}	Minimum Break-Before-Make Time	V _{IS} = 3.0 R _L = 300 Ω, C _L = 35 pF (Figure 1)	3.0	1.5	2	15						ns

C _{NC} Off C _{NO} Off C _{NC} On C _{NO} On	NC Off Capacitance, f = 1 MHz NO Off Capacitance, f = 1 MHz NC On Capacitance, f = 1 MHz NO On Capacitance, f = 1 MHz	Typical @ 25, $V_{CC} = 5.0$ V	$V_{CC} = 3.0$ V	pF
			208 102 547 431	

*Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted) (Note 6)

Symbol	Parameter	Condition	V_{CC} V	Typical	Unit
				25°C	
BW	Maximum On-Channel –3dB Bandwidth or Minimum Frequency Response	$V_{IN} = 0$ dBm V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	11.5	MHz
V_{ONL}	Maximum Feed-through On Loss	$V_{IN} = 0$ dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	–0.05	dB
V_{ISO}	Off-Channel Isolation	f = 100 kHz; $V_{IS} = 1$ V RMS; $C_L = 5$ nF V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	–65	dB
Q	Charge Injection Select Input to Common I/O	$V_{IN} = V_{CC}$ to GND, $R_{IS} = 0 \Omega$, $C_L = 1$ nF $Q = C_L - \Delta V_{OUT}$ (Figure 5)	3.0 5.0	15 20	pC
THD	Total Harmonic Distortion THD + Noise	$F_{IS} = 20$ Hz to 20 kHz, $R_L = R_{gen} = 600 \Omega$, $C_L = 50$ pF $V_{IS} = 1$ V RMS	3.0	0.14	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; $V_{IS} = 1$ V RMS, $C_L = 5$ pF, $R_L = 50 \Omega$ V_{IN} centered between V_{CC} and GND (Figure 4)	3.0	–81	dB

5. Off-Channel Isolation = $20 \log_{10} (V_{com}/V_{no})$, V_{com} = output, V_{no} = input to off switch.

6. –40°C specifications are guaranteed by design.

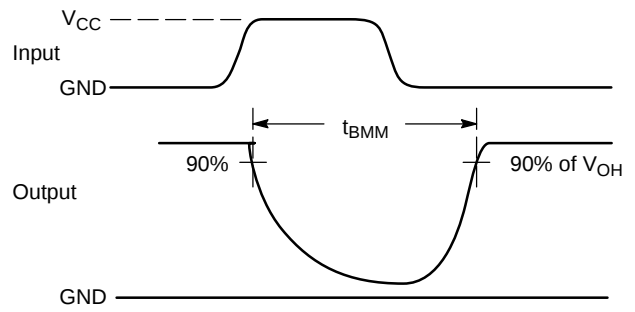
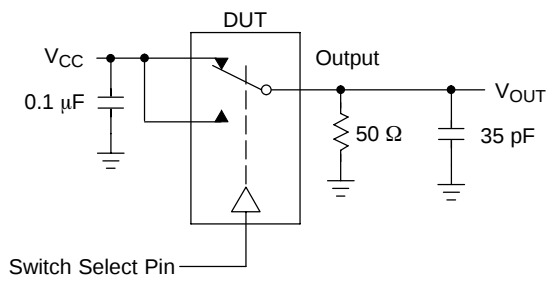


Figure 1. t_{BMM} (Time Break-Before-Make)

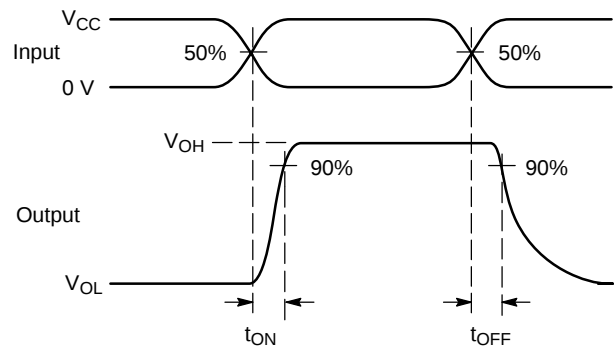
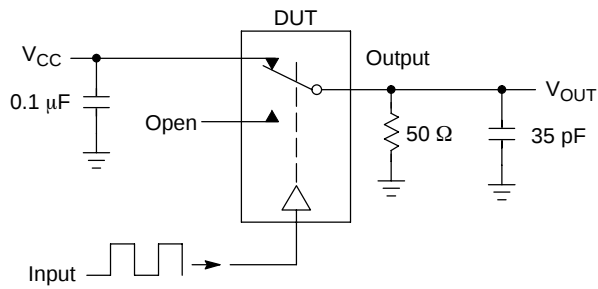


Figure 2. t_{ON}/t_{OFF}

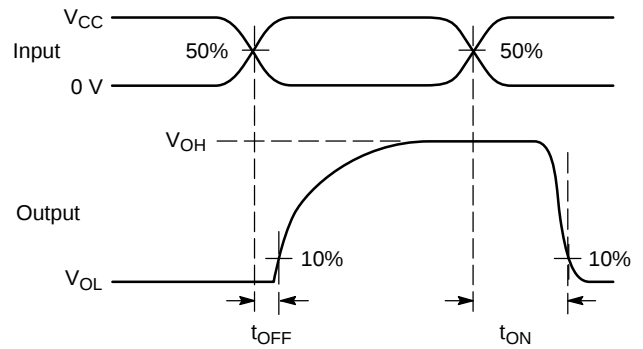
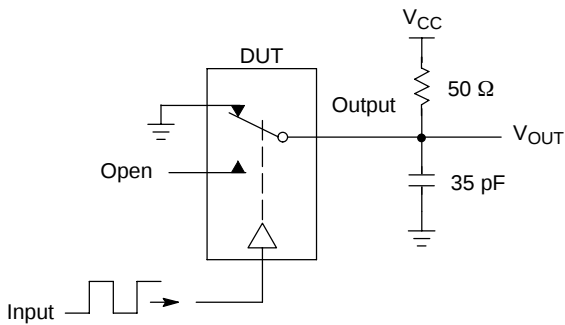
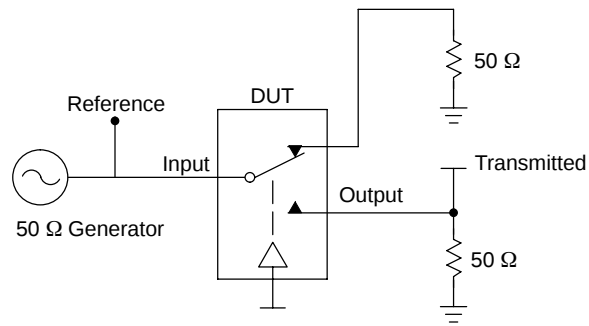


Figure 3. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 4. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ V_{ONL}

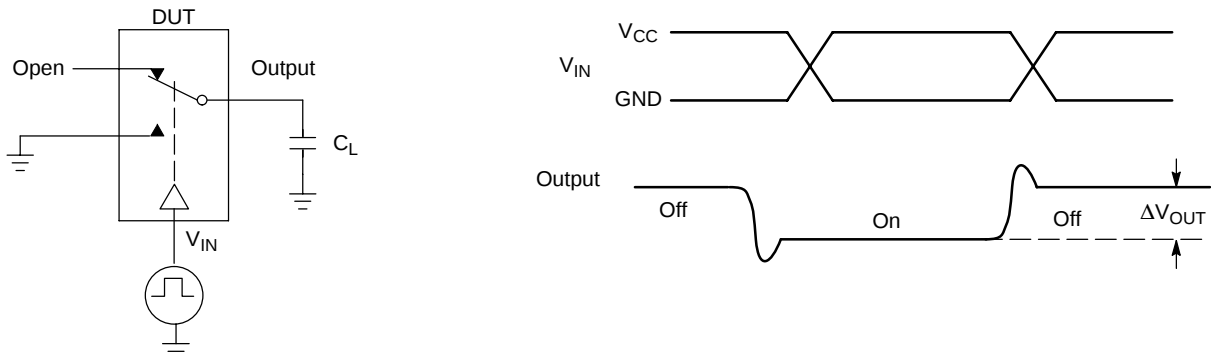


Figure 5. Charge Injection: (Q)

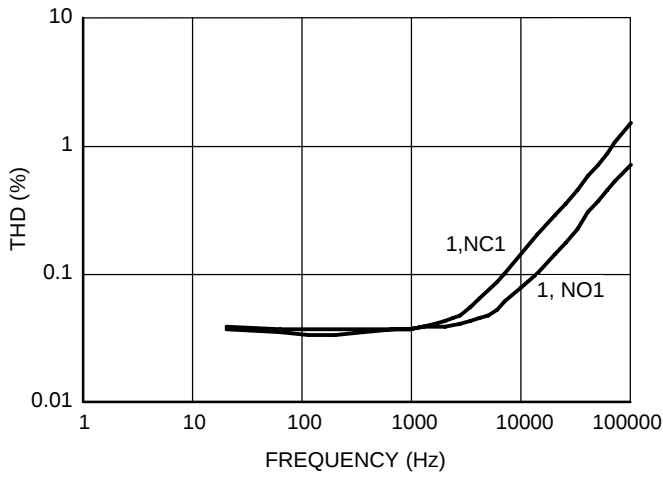


Figure 6. Total Harmonic Distortion Plus Noise versus Frequency

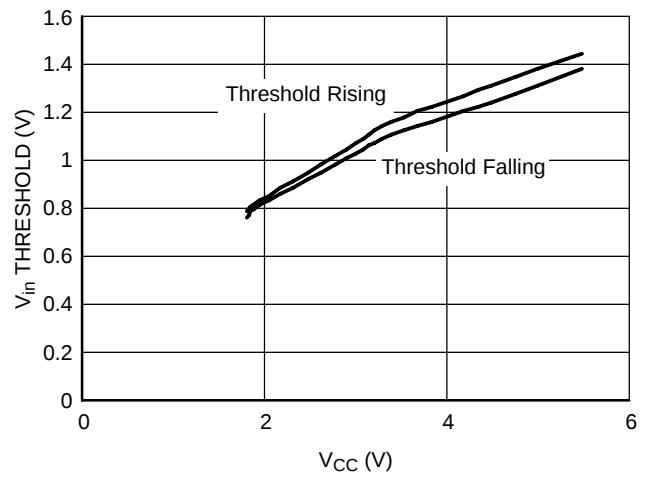


Figure 7. Voltage in Threshold on Logic Pins

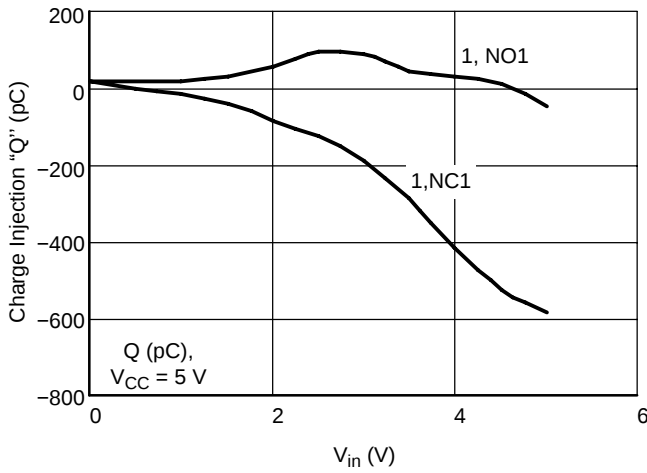


Figure 8. Charge Injection versus V_{is}

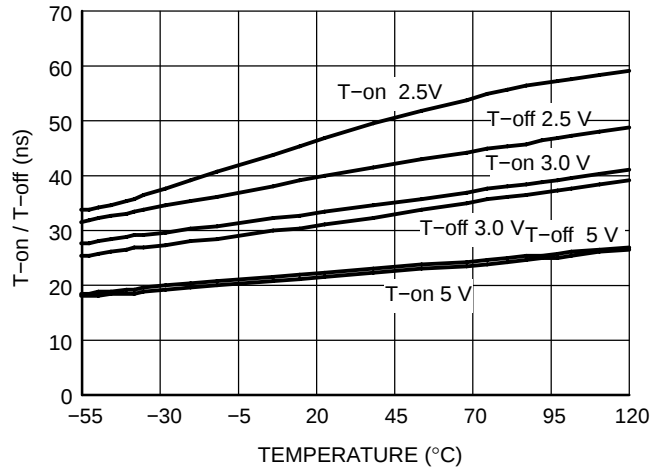


Figure 9. T-on/T-off Time versus Temperature

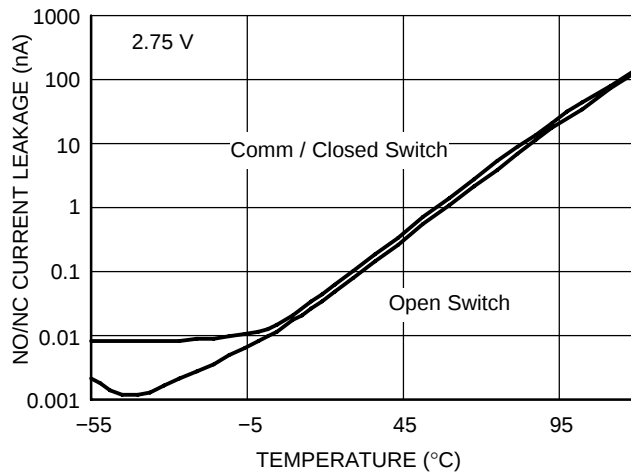


Figure 10. NO/NC Current Leakage Off and On, $V_{CC} = 5 V$

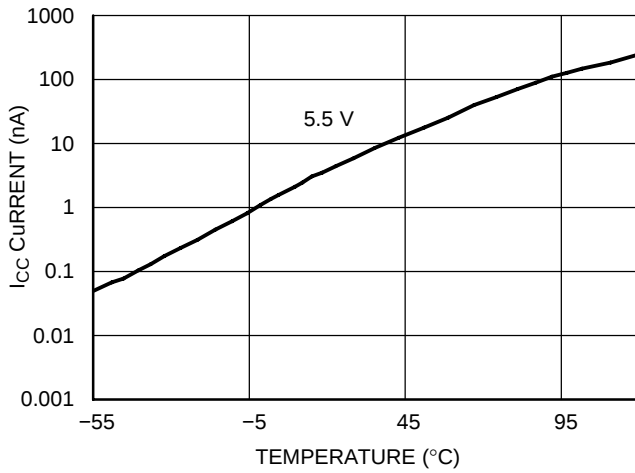


Figure 11. I_{CC} Current Leakage versus Temperature $V_{CC} = 5.5$ V

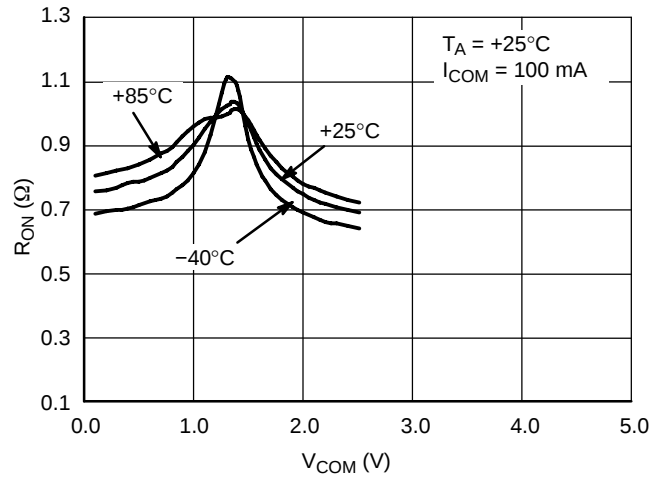


Figure 12. NC/NO On-Resistance versus COM Voltage

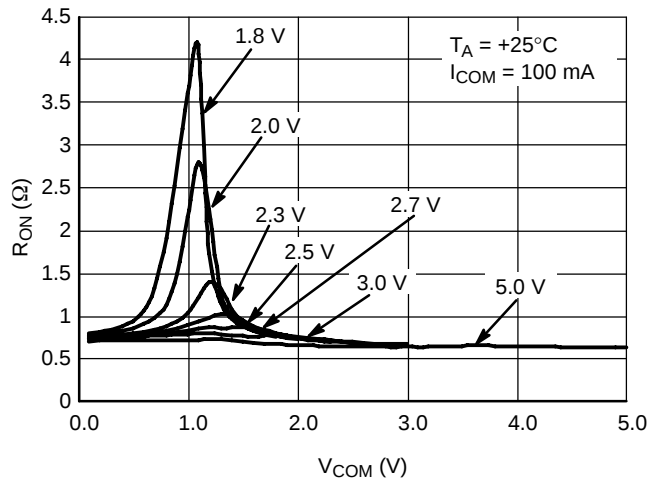


Figure 13. NC/NO On-Resistance versus COM Voltage

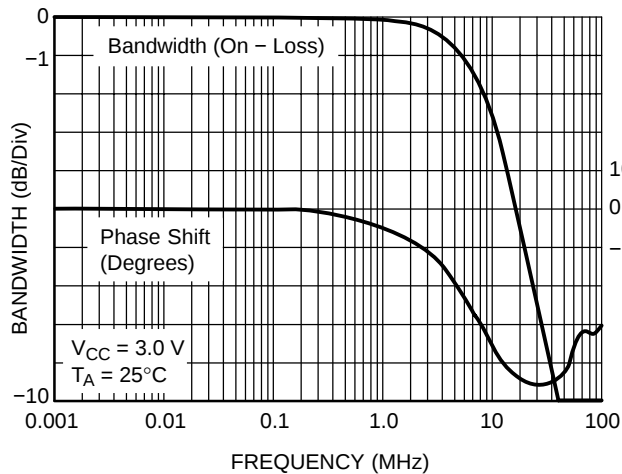


Figure 14. NC/NO Bandwidth and Phase Shift versus Frequency

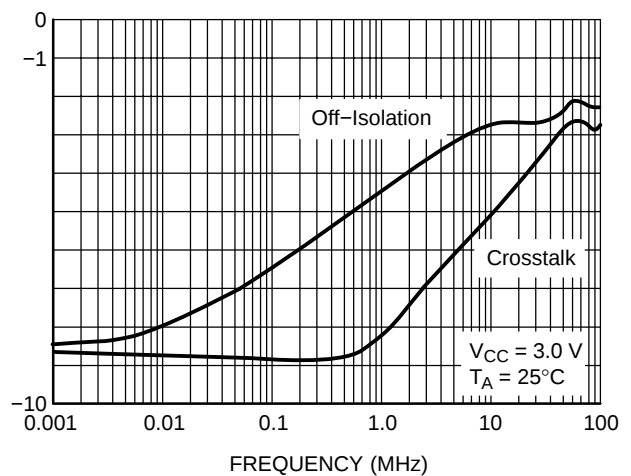


Figure 15. NC/NO Off Isolation and Crosstalk

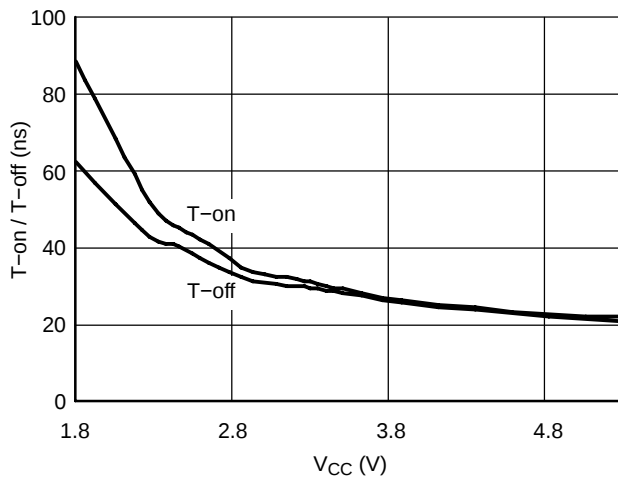


Figure 16. T-on/T-off versus V_{CC}

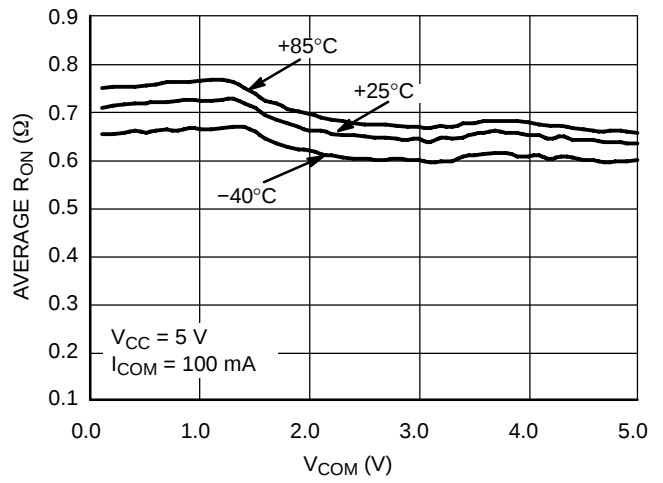


Figure 17. NC/NO On-Resistance versus COM Voltage

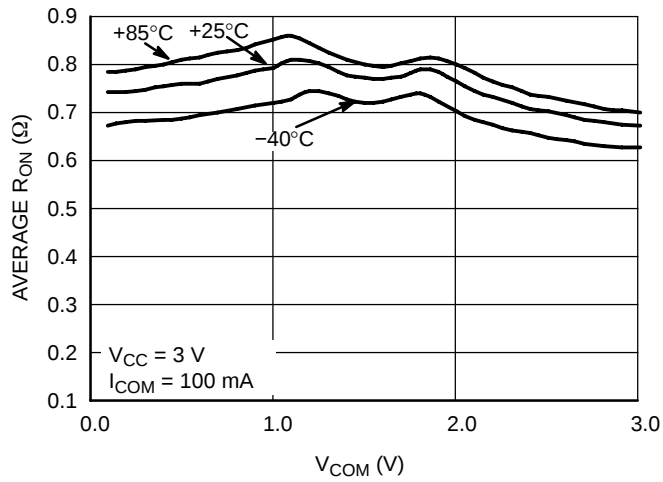


Figure 18. NC/NO On-Resistance versus COM Voltage

MECHANICAL CASE OUTLINE

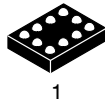
PACKAGE DIMENSIONS

ON Semiconductor®



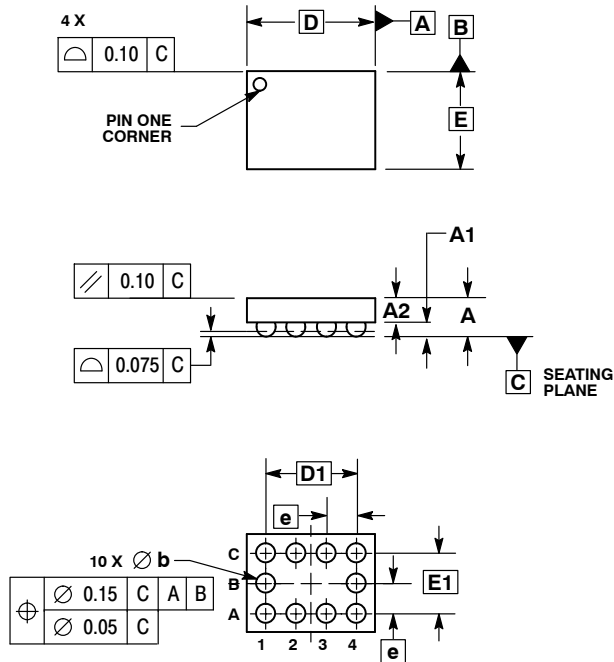
10 PIN FLIP-CHIP CASE 489AA-01 ISSUE A

DATE 04 MAY 2004



1

SCALE 4:1

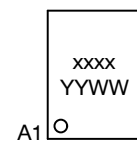


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

DIM	MILLIMETERS	
	MIN	MAX
A	---	0.650
A1	0.210	0.270
A2	0.280	0.380
D	1.965 BSC	
E	1.465 BSC	
b	0.250	0.350
e	0.500 BSC	
D1	1.500 BSC	
E1	1.000 BSC	

GENERIC MARKING DIAGRAM*



xxxx = Specific Device Code
YY = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98AON12946D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	10 PIN FLIP-CHIP	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative